Revealing Structure and Electronic Properties at Organic Interfaces Using TEM

James B. Gilchrist\textsuperscript{1}, Sandrine Heutz\textsuperscript{1}, David W. McComb\textsuperscript{2}

\textsuperscript{1} Imperial College London, Department of Materials, Exhibition Road, London, SW7 2AZ, UK
\textsuperscript{2} The Ohio State University, Materials Science and Engineering, Center for Electron Microscopy and Analysis, 1305 Kinnear Road, Columbus, OH 43212
j.gilchrist10@imperial.ac.uk, mccomb.29@osu.edu

Abstract
Molecules and atoms at material interfaces have properties that are distinct from those found in the bulk. Distinguishing the interfacial species from the bulk species is the inherent difficulty of interfacial analysis. For organic photovoltaic devices, the interface between the donor and acceptor materials is the location for exciton dissociation. Dissociation is thought to occur via a complex route effected by microstructure and the electronic energy levels. The scale of these devices and the soft nature of these materials provide an additional level of difficulty for analysis at these interfaces. The transmission electron microscope (TEM) and the spectroscopic techniques it incorporates can allow the properties of the donor-acceptor interfaces to be revealed. Cross-sectional sample preparation, using modern focused ion beam instruments, has been playing a key role in the progression of interfacial analysis. This powerful instrument combination has the ability to draw conclusions about interface morphology, structure and electronic properties of organic donor-acceptor interfaces at the molecular scale. Recent publications have demonstrated these abilities, and this article aims to summarise some of that work and provide scope for the future.

Introduction
Recent advances in the field of nanoscale electronic engineering have introduced new types of materials suitable for devices. One of the key material classes that are emerging as strong contenders to traditional silicon-based electronics are organics \textit{i.e.} those in which the principal elemental component is carbon. Some typical organic semiconductors include the phthalocyanines, fullerenes and their derivatives \textit{e.g.} PCBM and thiophene polymers \textit{e.g.} poly(3-hexylthiophene)(P3HT).

Organic photovoltaic (OPV) devices have the potential to provide a source of electric power. By using organic semiconductors as the principle photoactive materials, photovoltaics with lightweight and flexible properties could make a competitive alternative to current technology and fill niche applications.\cite{1–5} Organic devices have the added potential to be far cheaper to produce on large scales than comparable inorganic devices.\cite{6–9}
The typical structure for OPV devices consists of thin films of two materials, referred to as the (electron) donor and acceptor.[10] In the highest efficiency devices, these two materials are usually intimately mixed in a thin film as a ‘bulk heterojunction’ architecture but have also been developed as discrete thin films in a ‘bi-layer’ architecture.[11,12] Over the past half-century, it has been identified that the interface between the donor and acceptor materials is a key feature for photovoltaic power generation, and therefore of extreme technological interest.

Consensus surrounds the basic processes that occur within these devices that result in the generation of electrical power. These are outlined in Figure 1 a.[10]

![Diagram](image)

**Figure 1 a)** Fundamental processes occurring in an organic photovoltaic. 1. Photon absorption creating an exciton; 2. Exciton migration within the film; 3. Exciton dissociation into polarons; 4. Polaron migration to contacts. **b)** Proposed energy level diagram of processes occurring in a). Reprinted and adapted with permission from Brédas et al. Copyright 2009 American Chemical Society, in which the fine electronic structure of the charge transfer state is shown.[13]

The total efficiency of a device is a combination of the proportion of the energy that is transferred through all these processes. Increasing the efficiency of OPV devices has focused on optimising these individual processes, whether its increasing absorption, dissociating more excitons or reducing the resistance polarons experience.[14,15]

The mechanisms in which photons are absorbed and excitons migrate within the films via the Förster and Dexter models are fairly well understood.[10,13,16–18] However, as of yet the mechanism of exciton dissociation has not yet been fully described.[13] From a number of recent publications, it has been proposed that dissociation could occur by the transfer of the excited electron to a ‘charge transfer state’ (CTS), before either relaxation to the ground state (referred to as recombination) or separation into free charges (Figure 1 b).[19–22]

Efficient exciton separation within the CTS, which would lead to more efficient devices, appears to be highly dependent on the microstructure, electronic energy levels and morphology of the donor-acceptor interface. Interfacial characterisation in terms of these aspects is, therefore, vital to guide further development of OPV devices.

Analysing these technologically relevant interfaces is incredibly challenging due to the scale of the thin films produced (typically 10 – 300 nm), the soft nature of the materials used and inherent problems of interfacial analysis. Acquiring data about the aforementioned characteristics can be problematic. Many techniques aim to collect data from bulk samples and infer characteristics of the interface.[23–25] Useful as these techniques are, they do not provide the spatial resolution needed to make claims about the organic interface on the molecular/atomic scale. Gaining an understanding at this scale, for example elucidating specific locations where excitons dissociate/recombine, could drive theoretical and synthetic experimentation to improve device performance.
Transmission electron microscopy (TEM) has the ability to resolve these morphological and structural features which could aid the understanding of interfaces in OPVs. Indeed, high-resolution transmission electron microscopy (HRTEM) has been used extensively in OPV research in recent years.[12,26,27] However accounting for artefacts introduced during specimen preparation and data acquisition in the TEM must be undertaken. In addition to this, there is further potential to probe morphology, crystal and electronic structure of donor-acceptor materials and interfaces, with high spatial resolution using HRTEM, high-resolution scanning transmission electron microscopy (HRSTEM) and the associated spectroscopies: energy dispersive X-ray (EDX) spectroscopy, electron energy loss spectroscopy (EELS) and energy filtered TEM (EFTEM), physical explanations of which can be found below. The clear target for this analysis would be the search for and the probing of the fine electronic structure proposed in the CTS.[13] Morphological and electronic characterization on this scale is rapidly developing. This article and the accompanying one by Goode et al. identifies some recent work showcasing progress within the field of interfacial characterization using spectroscopy.[28–30]

**Imaging Organics in the TEM**

Imaging organic materials in the TEM can reveal the microstructure and morphology. However, damage to the material through bond scission (radiolysis), atomic displacement (knock-on damage) and specimen heating can take place.[31–33] Organic materials tend to be composed mainly of low-mass elements and are highly susceptible to these damage mechanisms. This susceptibility can vary enormously depending on the chemical structure, the type of bonding present and molecular orientation with respect to the electron beam. The critical dose for metal-free phthalocyanine, copper phthalocyanine (CuPc) and hexadecachloro copper phthalocyanine (Cl_{16}CuPc) can vary by two orders of magnitude with changes in the chemical structure.[34,35] Although it is difficult to identify a direct relationship between chemical structure and damage susceptibility in organic materials, aromatic and halogenated species appear to be less prone to degradation than aliphatic and non-halogenated analogues.

The energy of the electron beam can also have an effect on the damage inflicted on the sample material. Hayashida et al. demonstrated that the critical dose for CuPc increased with increasing accelerating voltage.[36] This suggests that for CuPc, radiolysis is the dominant damage mechanism. It, therefore, follows that higher beam energies should be used for imaging aromatic organic materials. In the same report, however, Hayashida et al. also demonstrated a diminishing contrast with increasing incident beam energies. Therefore, a major challenge for TEM characterisation of organic materials is to optimise data collection parameters.[37]

Provided that sample damage can be controlled and accounted for, astonishing data can be collected. Images purporting to resolve the molecular structure of phthalocyanines have been reported since the 1970s.[38,39] Recently, the resolution capabilities of HRSTEM has been exemplified through the work of Haruta and Kurata where the sub-molecular structure has been resolved in Cl_{16}CuPc (Figure 2).[40,41]
Figure 2 a) Molecular structure and unit cell viewed down the c-axis of Cl₁₆CuPC with a schematic showing the relationship between the incident electron beam and the molecular stack. b) HRSTEM image of a 30 - 40 nm thick Cl₁₆CuPc film. The brightest spots indicate the location of central copper atom stacks. The less intense spots surrounding each of these indicate the location of the 16 chlorine atoms. c) On translational averaging and d) noise filtering, the carbon ring structure of the phthalocyanine becomes visible. Reprinted and adapted with permission from Haruta et al. Copyright 2008 Elsevier and from Haruta and Kurata Copyright 2012 Nature Publishing group.[40,41]

Revealing the Interface

Investigating the organic-organic interface at the atomic/molecular level is challenging. While TEM and scanning transmission electron microscopy (STEM) techniques have the resolution capabilities, when bi-layer film structures are prepared on thin support TEM grids, the beam is transmitted through the specimen, superimposing information from the bulk materials over the interface. Probing the interface between different materials by growing planar heterostructures and examining the stack in top view might simplify the preparation procedure, but makes the analysis/interpretation significantly more difficult as it now becomes almost impossible to distinguish the interfacial species from the relatively large number of bulk species (Figure 3 a).
Superimposed information can be mitigated by preparing samples in which the ratio of interface-to-bulk species is maximised i.e. by intimately mixing the two materials (as used for bulk heterojunction OPV architectures), and deducing the interfacial properties by comparing images or spectra with those of pure materials (Figure 3 b).[11] Pfannmöller et al. used a similar approach to analyse P3HT:PCBM bulk-heterojunction films using electron spectroscopic imaging.[42] However, phase separation of materials can occur, increasing the number of bulk species that the incident beam interacts with. Increasing the ratio of interface-to-bulk species is vital for accurate analysis of the interface in mixed films. Provided that phase separation is taken into account, useful information can be gathered, that suggests that this preparation technique can be used to investigate interface species as well as phase separation itself.[42] This approach has the potential to provide a quicker and easier sample preparation procedure, and result in data that would drive further research.

Sample preparation approaches which involve exposing the interface for direct examination in the TEM could provide information about interfaces since superimposed information is avoided. By cross-sectioning planar film architectures such that in the TEM the incident electron beam is parallel to the interface of interest, the bulk material and interface can be analysed and interpreted separately (Figure 3 c). The new challenge now becomes the preparation of the cross-sectional specimen that displays the interface in its native state.

Material cross-sectioning has been traditionally performed using two routes: ultramicrotomy and ion beam milling. Ultramicrotomy involves the sectioning of material, typically embedded in a supporting resin with a microscopic knife and floating on the surface of a liquid bath. This technique is typically used for preparing TEM samples of biological specimens and works best for samples with hardness’s that can be matched to that of the resin. However, for organic films grown on hard substrates, e.g. silicon, indium doped tin oxide, ultramicrotomy is unsuitable for preparing cross-sectional TEM samples since large scale mechanical damage occurs. The scale of damage observed in
the work of Domanski et al. and Nonaka et al. is great, revealing the delamination of organic films from contacts and cracking of substrates.[43,44] In addition to this, Jantou et al. demonstrated the resolution enhancement when a focused ion beam (FIB) is used to prepare specimens as opposed to ultramicrotomy.[45]

An alternative method to ultramicrotomy uses a beam of accelerated ions which sputters away material from the specimen gradually creating an electron transparent foil. Ion beam milling is generally performed using either a broad beam of argon ions or a focused beam of gallium ions. For materials which are less prone to amorphization, sample preparation using an ion beam can be relatively straightforward. However, for organic materials, significant amorphization is expected. Therefore, for the high-resolution examination of the organic-organic interface, steps must be taken to minimize amorphization during sample preparation. It has been demonstrated in the work by Dürr et al. using broad argon ion beam milling in combination with epoxy embedding and Herzing et al. and Gilchrist et al. using more modern dual beam FIB systems following the in situ lift-out procedure, that organic materials can be prepared whilst retaining crystallinity, a sign that significant amorphization has not occurred.[12,27,46] For CuPc/C_{60} bilayers prepared in this manner, crystallinity is observed extensively (Figure 4 a – d).[12] The TEM damage mechanisms mentioned above are also present in sample preparation using an accelerated ion beam. Since bond scission and atomic displacement would alter the electronic structure found in materials, this damage must be minimized in order to probe electronic structure found at a donor-acceptor interface. In addition to this, specimen heating could also induce a phase change or drive material mixing/segregation.

Figure 4 a) Cross-sectional HRTEM image from a CuPc/C_{60} bi-layer, where lattice fringes in both the CuPc and C_{60} can be identified. b) In the C_{60} layer lattice fringes corresponding to the (111) and (200) planes can be observed (0.80 and 0.48 nm respectively). c) The interface between the CuPc and C_{60} is not clear despite lattice fringes from both materials being observed. d) In the CuPc film lattice fringes from both the (100) and the (001) planes (1.3 and 1.2 nm respectively). In regions where both fringes are observed, the beam is close to parallel to the molecular stack. Scale bar in d) applies to b) and c).

For FIB sample preparation damage reduction methodologies involve decreasing the accelerating voltage, beam current and the angle the beam makes with the thin foil during the final thinning stages.[12,47,48] This can be thought of as reducing the kinetic energy and flux of incident ions perpendicular to the foil. The well-known work by Mayer et al. demonstrates the effects of reducing the energy of incident ions using HRTEM imaging.[47] Here, the amorphous material that surrounds a foil (an indicator of the damage) reduces from 22 to 0.5 – 1.5 nm when beam energy is decreased from 30 keV to 2 keV during final thinning stages. Similarly, the work by Prenitzer et al. and Ishitani et al. clearly describe the improvement of feature milling and ion penetration depth at lower beam
currents and shallower incident angles.[48,49] The success of these methodologies in the context of organic electronics has further been established by Gilchrist et al., using thin film structures composed of CuPc and C₆₀, where structure and morphology have been observed in unprecedented detail using HRTEM (Figure 4).[12]

In addition to these methods, cryo-FIB prepares thin foils at ultra-low temperatures. Similar to the damage reduction that is observed by cooling the foil during TEM imaging, the low temperatures reduce the likelihood that molecular bond breakage occurs, and thus retains the crystal structure for longer when exposed to identical conditions. Cryo-FIB has been employed recently in the work by Marko et al. and Edwards et al. who examined the effects of controlling the temperature rise of samples containing ice while thinning using a FIB at liquid nitrogen temperatures.[50,51] The cryo-FIB was able to prepare foils of hydrated cells and vitreous ice without devitrification. In addition to these results, the work by Bassim et al. used foils of lignite coal and polyacrylamide, prepared using cryo-FIB, in which the fine electronic structure can be retained and examined using X-ray absorption spectroscopy.[52] These results suggest that by using cryo-FIB methods, foils of organic thin films could be prepared in which the electronic structure is retained, and full implementation of the commonly used lift-out technique is starting to be employed under cryo conditions.[53] For the interfaces present in OPVs, sample preparation using a FIB in combination with damage reduction techniques, demonstrate that TEM samples could be prepared for analysis of the electronic structure at interfaces.

**Spectroscopic Analysis**

The resolution capabilities of TEM and STEM, in combination with carefully dosed imaging and cross-sectioning methods, have allowed structural and morphological information about the organic-organic interface to be obtained. From the work by Gilchrist et al. different materials in archetypical photovoltaic devices can be identified using contrast from crystalline regions (phase contrast) within CuPc and C₆₀ in cross-section.[12] On examination of the CuPc film, features observed within the film show a remarkable similarity to those observed in earlier work by Kobayashi et al. and Fryer et al. on various phthalocyanine films in top view.[31,54–56] This further demonstrates that the cross-sectional methodology described by Gilchrist et al. yields TEM foils without significant damage to the crystal structure.[12] Lattice fringes also observed in the C₆₀ film enable the clear distinction between the bulk materials. However, the interface between these materials is still unclear (Figure 4c). On initial inspection the lack of lattice fringes could be thought of as the interface being comprised of an amorphous interlayer. By using EDX in combination with STEM, the complexity of this interface is revealed; nanoscale morphology extending within the thickness of the foil which is superimposed in the two-dimensional image. The morphology observed at this interface has a similar route mean square roughness to that of individual CuPc films grown under otherwise identical conditions and suggests that diffusion of the molecular species does not occur, creating a chemically sharp, but morphologically rough interface.

In bulk-heterojunction polymer devices, the morphology of the organic films can be extremely complex and have dramatic consequences for device efficiency.[57] Additionally, these types of film are usually less crystalline and make phase contrast, as a mechanism of interface identification, inappropriate. Moench et al. investigated the morphology changes occurring in these systems as a function of substrate temperature using STEM EDX.[58] Mixed DCVST-Me (a sulfur-containing
polymer) and C_{60} films were grown at room temperature (RT), 80 and 140 °C. At RT, the donor and acceptor materials are highly intermixed and result in devices with intermediate short circuit currents (J_{sc}, indicating lower charge extraction) and efficiencies (Figure 5 a and b). At 80 °C, the active layer forms a more desirable morphology, with carbon islands around 10 nm in size dispersed within a sulfur-rich (DCVST-Me) network (Figure 5 c and d). A balance between interfacial area and charge extraction is achieved. Device electrical characteristics further support this with increases in J_{sc} and the fill factor, overall leading to a higher efficiency. For substrate temperatures of 140 °C, an undesirable morphology is promoted (Figure 5 e and f). Here, in addition to large film thickness variations, larger scale phase separation is observed further reducing the interfacial area with a loss of percolation pathways also expected. The papers of Gilchrist et al. and Moench et al., expertly demonstrate STEM EDX methods for characterising the nanoscale morphology of organic-organic heterostructures.[12,58]
One of the major disadvantages of current EDX technology in the TEM is the need for high levels of irradiation to achieve a low error in the quantification results. During collection, therefore, phase separation through sample heating might be occurring in addition to radiolytic damage and atomic displacement. Additionally, the spatial resolution of STEM EDX mapping will be limited by the relatively large interaction volume formed as the beam passes through the specimen. This, therefore, means molecular scale discoveries about organic donor-acceptor interfaces lie beyond the abilities of current STEM EDX methods.
Spectroscopy and imaging methods utilising transmitted, inelastically scattered electrons, on the other hand, yield a far higher spatial resolutions. Electrons can lose energy to the sample, exciting electronic transitions in atoms and molecules in the beam path. The transmitted electrons that have lost part (or even all) of their energy can be separated by a magnetic filter and recorded using a camera. Integrating across the image produced, results in a spectrum showing the distribution of electrons as a function of energy loss. This technique is referred to as electron energy loss spectroscopy (EELS). Additionally, using the same magnetic filter, an image can be produced, which is only formed by electrons that have lost a particular energy range, highlighting spatial regions where particular transitions occurred. This techniques is energy filtered TEM (EFTEM).

Some transitions are characteristic of different materials, and detection can be highly sensitive, for example in the low-loss energy range (typically between 1 – 50 eV energy loss) allowing for lower doses to be used. Provided that spectra can be assigned to a material type, EELS and EFTEM can be used to provide morphological characterisation on the molecular/atomic scale, and is especially useful for the analysis of light elements.

An example of this sensitivity can be seen in the work by Guo et al. which shows unique spectra from the materials P3HT, PCBM and PGeBTBT (a germanium containing copolymer) in the valence-loss regions of the EEL spectrum (Figure 6 a). The sensitivity of the material to electron dose is also demonstrated by acquiring spectra from the three materials at increasing electron dose. For all material types an inverse relationship between peak intensity and dose is found (Figure 6 b, c and d). This relationship is attributed to the electronic structure of the material degrading under electron beam irradiation.

The group also present the morphological analysis of P3HT:PCBM mixed films showing the scale of phase separation between the two materials using EFTEM imaging (Figure 3). When compared to the STEM EDX data by Moench et al. (above) the scale of the phase separation is similar, however,
the EFTEM data has been collected at a fraction of the dose. In this case below the critical dose of P3HT.[58,59]

![EFTEM Imaging](image)

Figure 7 EFTEM imaging of P3HT/PCBM (1:1) mixed film using the low-loss energy region, scale bar represents 100 nm. Following processing using principle component analysis the P3HT rich (a) and PCBM rich (b) regions are identified. A composite image formed from (a) and (b). Reprinted and adapted with permission from Guo et al. Copyright 2015 John Wiley and Sons Inc.[59]

For the EFTEM work by Guo et al., the characteristic valence electronic structure from the different species has been used to map distribution. This, however, does not identify the fine electronic structure expected to exist at the donor-acceptor interface. One of the reasons for this is the relatively low energy resolution of these techniques. Higher energy resolutions should enable CTS to be identified and mapped and correlated to morphological or structural features. Energy resolutions of 10 – 20 meV have been reported and applied to probing vibrational states in various materials and even mapping of band-gap excitations at MoS2/MoSe2 interfaces. [30,60] The improvement expected in future TEMs equipped with electron energy filters should enable CTS to similarly be mapped to drive device improvement.

Conclusions

The current status of using TEM to probe organic materials and interfaces has been demonstrated in the featured articles. STEM in combination with EDX shows great potential to expose phase distributions between chemically distinct species. The results from Gilchrist et al. and Moench et al. demonstrate that the nanoscale morphology can be revealed in mixed films and at discrete interfaces.[12,58] Following the results from Guo et al., the use of low-loss transitions in the EELS spectrum has allowed nanoscale morphology to be probed at unprecedented low doses.[59] Cross-sectional FIB preparation of TEM samples has advanced to a point where relatively pristine TEM foils of ideal soft-soft interfaces can be prepared. With the advent of cryo-FIB, damage of the electronic structure of organic materials can be reduced further. With continuing advances made in TEM spectroscopy, higher energy resolution EELS and EFTEM will be key in exposing the mysteries of organic-organic interfaces.

References


Drori T, Sheng CX, Ndobe A, Singh S, Holt J, Vardeny Z V. Below-gap excitation of pi-


Ishitani T, Umemura K, Ohnishi T, Yaguchi T, Kamino T. Improvements in performance of


